

MOSFETs Silicon P-Channel MOS (U-MOSVI)

TPCP8107

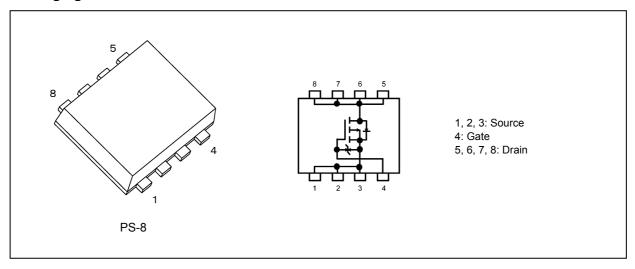
1. Applications

- · Motor Drivers
- · Mobile Equipment

2. Features

- (1) AEC-Q101 qualified
- (2) Small, thin package
- (3) Small gate charge: $Q_{SW} = 14.0 \text{ nC (typ.)}$
- (4) Low drain-source on-resistance: $R_{DS(ON)} = 13.9 \text{ m}\Omega$ (typ.) ($V_{GS} = -10 \text{ V}$)
- (5) Low leakage current: $I_{\rm DSS}$ = -10 μA (max) (V_{\rm DS} = -40 V)
- (6) Enhancement mode: V_{th} = -2 to -3 V (V_{DS} = -10 V, I_D = -1 mA)

3. Packaging and Internal Circuit





4. Absolute Maximum Ratings (Note) (Ta = 25°C unless otherwise specified)

Character	Symbol	Rating	Unit		
Drain-source voltage			V _{DSS}	-40	V
Gate-source voltage			V _{GSS}	-20/+10	
Drain current (DC)		(Note 1)	I _D	-8	Α
Drain current (pulsed)		(Note 1)	I _{DP}	-32	
Power dissipation	(t = 5 s)	(Note 2)	P _D	2.01	W
Power dissipation	(t = 5 s)	(Note 3)	P _D	1	W
Single-pulse avalanche energy		(Note 4)	E _{AS}	145.8	mJ
Avalanche current			I _{AR}	-8	Α
Channel temperature		(Note 5)	T _{ch}	175	°C
Storage temperature		(Note 5)	T _{stg}	-55 to 175	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

5. Thermal Characteristics

Characteristics	Symbol	Max	Unit		
Channel-to-ambient thermal resistance	(t = 5 s)	(Note 2)	R _{th(ch-a)}	74.6	°C/W
Channel-to-ambient thermal resistance	(t = 5 s)	(Note 3)		150	

Note 1: Ensure that the channel temperature does not exceed 175°C.

Note 2: Device mounted on a glass-epoxy board (a), Figure 5.1

Note 3: Device mounted on a glass-epoxy board (b), Figure 5.2

Note 4: V_{DD} = -25 V, T_{ch} = 25°C (initial), L = 2.366 mH, R_{G} = 25 Ω , I_{AR} = -8 A

Note 5: The definitions of the absolute maximum channel and storage temperatures are qualified per AEC-Q101.

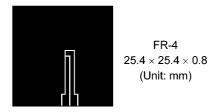


Fig. 5.1 Device Mounted on a Glass-Epoxy Board (a)

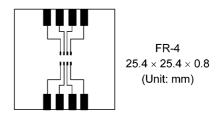


Fig. 5.2 Device Mounted on a Glass-Epoxy Board (b)

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.



6. Electrical Characteristics

6.1. Static Characteristics (T_a = 25°C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I _{GSS}	V _{GS} = -16/+10 V, V _{DS} = 0 V	_	_	±10	μА
Drain cut-off current	I _{DSS}	V _{DS} = -40 V, V _{GS} = 0 V	_	_	-10	
Drain-source breakdown voltage	V _{(BR)DSS}	I _D = -10 mA, V _{GS} = 0 V	-40	-	1	V
Drain-source breakdown voltage (Note 6)	V _{(BR)DSX}	$I_D = -10 \text{ mA}, V_{GS} = 10 \text{ V}$	-30	_		
Gate threshold voltage	V_{th}	$V_{DS} = -10 \text{ V}, I_D = -1 \text{ mA}$	-2	-2.5	-3	
Drain-source on-resistance	R _{DS(ON)}	$V_{GS} = -6 \text{ V}, I_D = -4 \text{ A}$	_	16.8	26.8	mΩ
		V _{GS} = -10 V, I _D = -4 A	_	13.9	18	

Note 6: If a reverse bias is applied between gate and source, this device enters $V_{(BR)DSX}$ mode. Note that the drain-source breakdown voltage is lowered in this mode.

6.2. Dynamic Characteristics (T_a = 25°C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C _{iss}	V _{DS} = -10 V, V _{GS} = 0 V, f = 1 MHz	_	2160	_	pF
Reverse transfer capacitance	C _{rss}		_	238	_	
Output capacitance	C _{oss}		_	292		
Switching time (rise time)	t _r	See Figure 6.2.1.	_	11	_	ns
Switching time (turn-on time)	t _{on}		_	29	_	
Switching time (fall time)	t _f		_	35	_	
Switching time (turn-off time)	t _{off}		_	150		

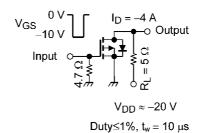


Fig. 6.2.1 Switching Time Test Circuit

6.3. Gate Charge Characteristics (T_a = 25°C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Q_g	$V_{DD} \approx -32 \text{ V}, V_{GS} = -10 \text{ V}, I_{D} = -8 \text{ A}$	_	44.6		nC
Gate-source charge 1	Q _{gs1}			5.7		
Gate-drain charge	Q_{gd}		_	13.1		
Gate switch charge	Q_{SW}		_	14.0	_	

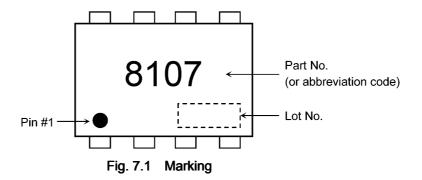
6.4. Source-Drain Characteristics (T_a = 25°C unless otherwise specified)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Reverse drain current (pulsed)	(Note 7)	I _{DRP}	_	_	_	-32	Α
Diode forward voltage		V_{DSF}	I _{DR} = -8 A, V _{GS} = 0 V	_	_	1.2	٧

Note 7: Ensure that the channel temperature does not exceed 175°C.



7. Marking



8. Characteristics Curves (Note)

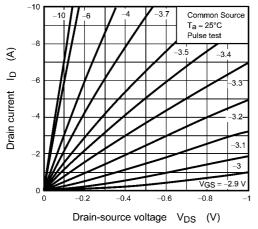


Fig. 8.1 I_D - V_{DS}

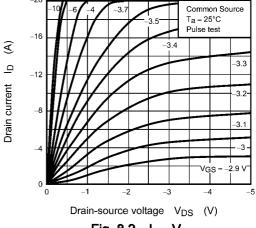


Fig. 8.2 I_D - V_{DS}

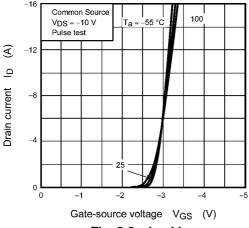


Fig. 8.3 I_D - V_{GS}

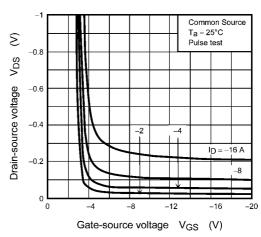


Fig. 8.4 V_{DS} - V_{GS}

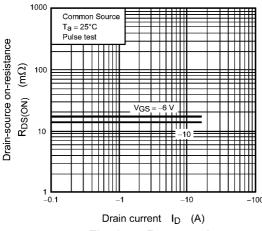


Fig. 8.5 R_{DS(ON)} - I_D

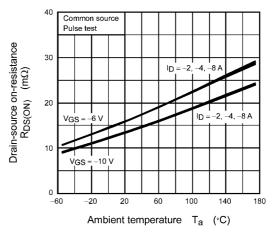


Fig. 8.6 R_{DS(ON)} - T_a (Note 8)

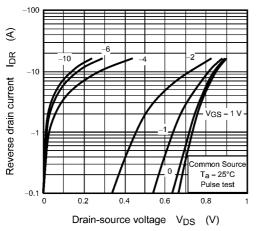


Fig. 8.7 IDR - VDS

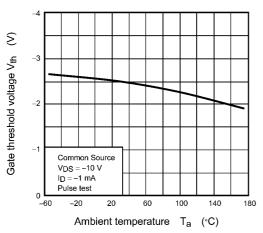


Fig. 8.9 V_{th} - T_a (Note 8)

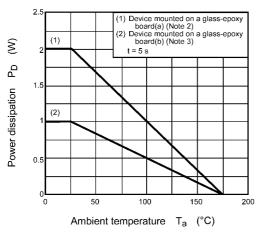


Fig. 8.11 P_D - T_a (Guaranteed Maximum) (Note 8)

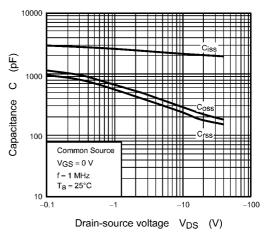


Fig. 8.8 Capacitance - V_{DS}

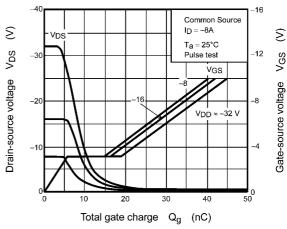


Fig. 8.10 Dynamic Input/Output Characteristics

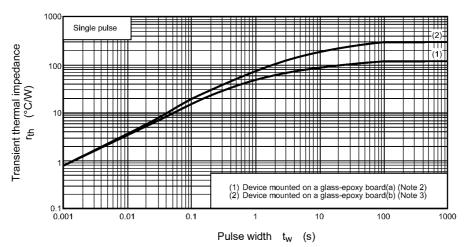


Fig. 8.12 r_{th} - t_w (Guaranteed Maximum)

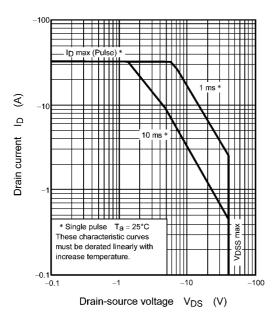


Fig. 8.13 Safe Operating Area (Guaranteed Maximum)

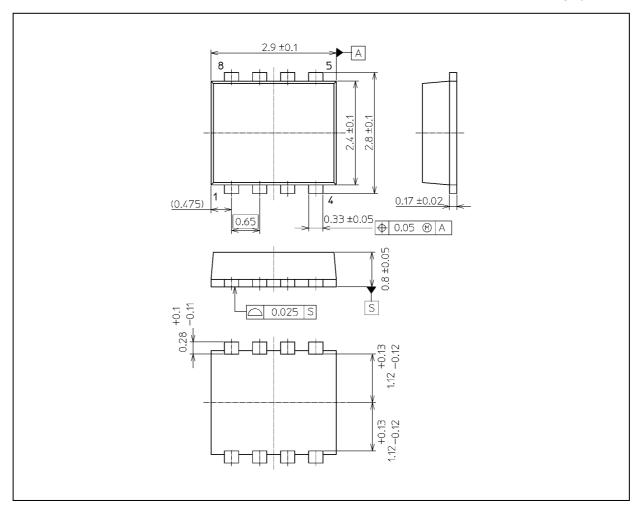
Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

Note 8: The definitions of the absolute maximum channel and storage temperatures are qualified per AEC-Q101.



Package Dimensions

Unit: mm



Weight: 0.017 g (typ.)

	Package Name(s)	
TOSHIBA: 2-3V1S		
Nickname: PS-8		



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